

Fig. 4

BEST AVAILABLE COPY

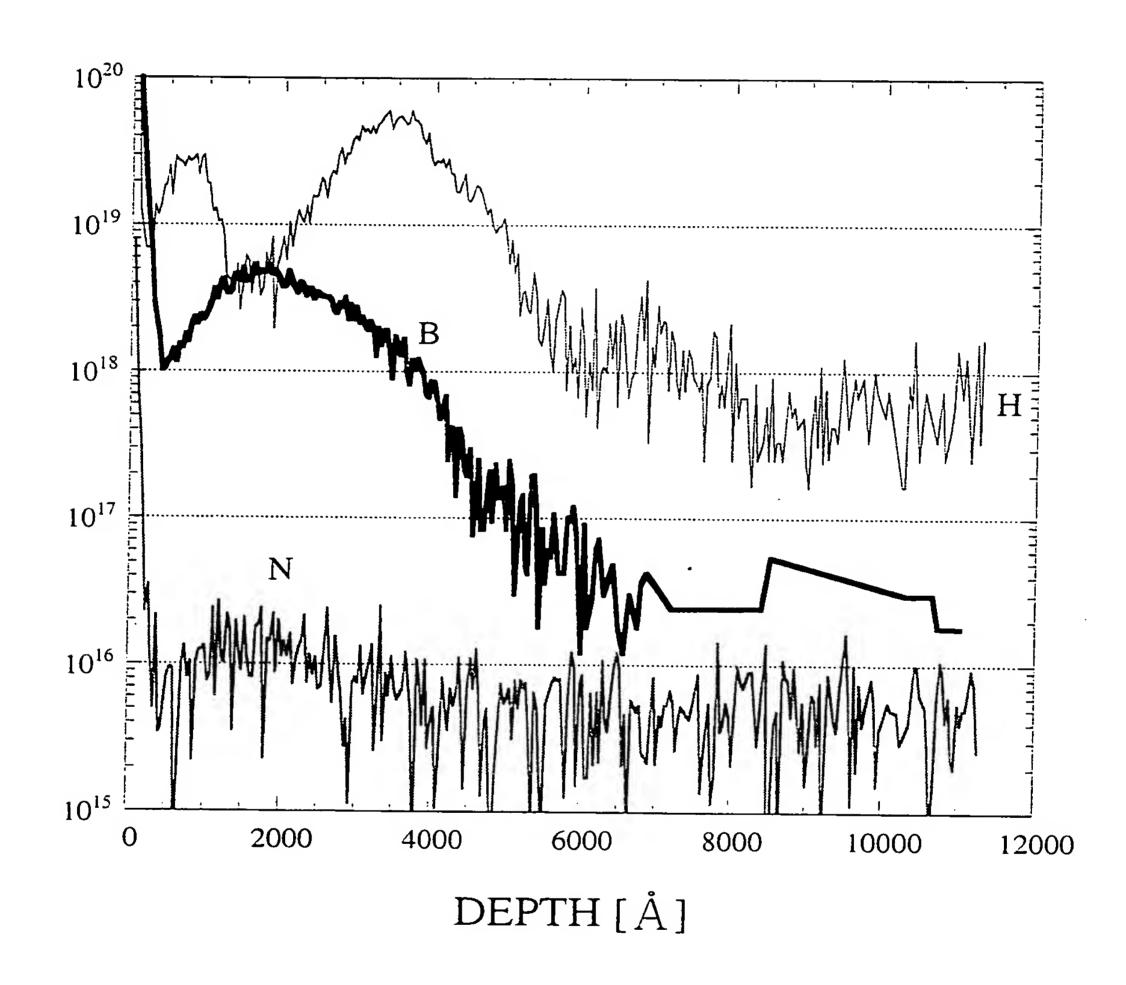


Fig. 2

CONCENTRATION[atoms/cm³]

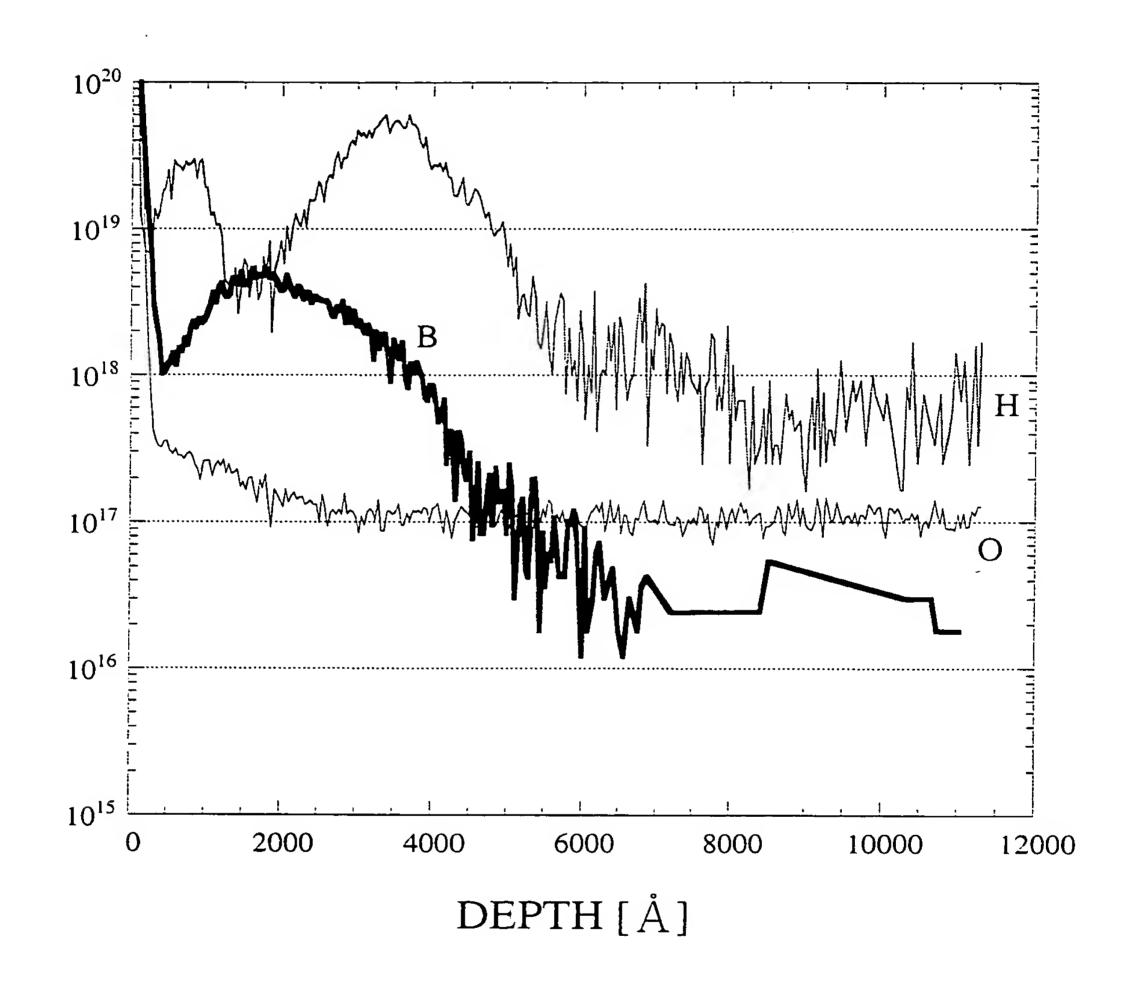
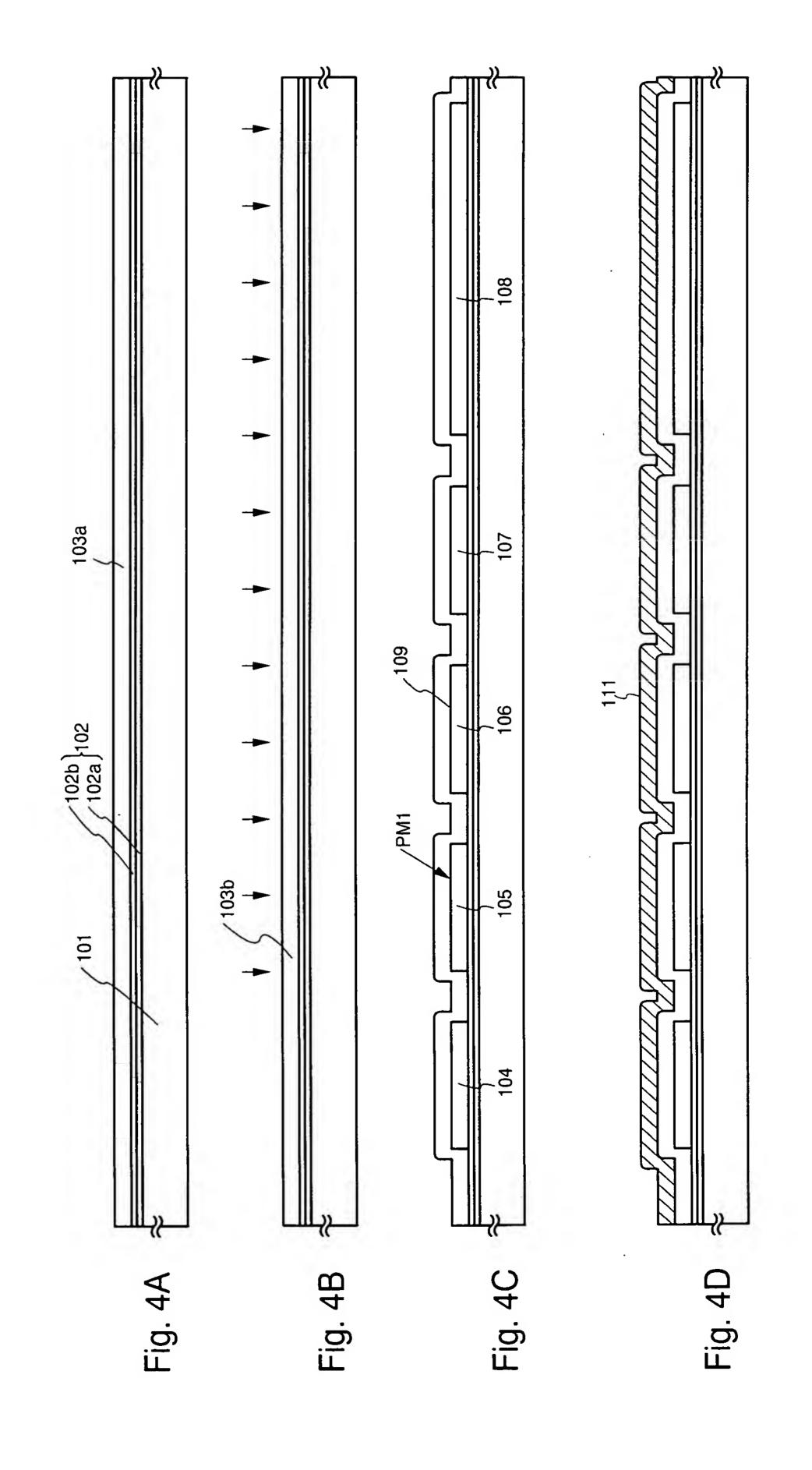
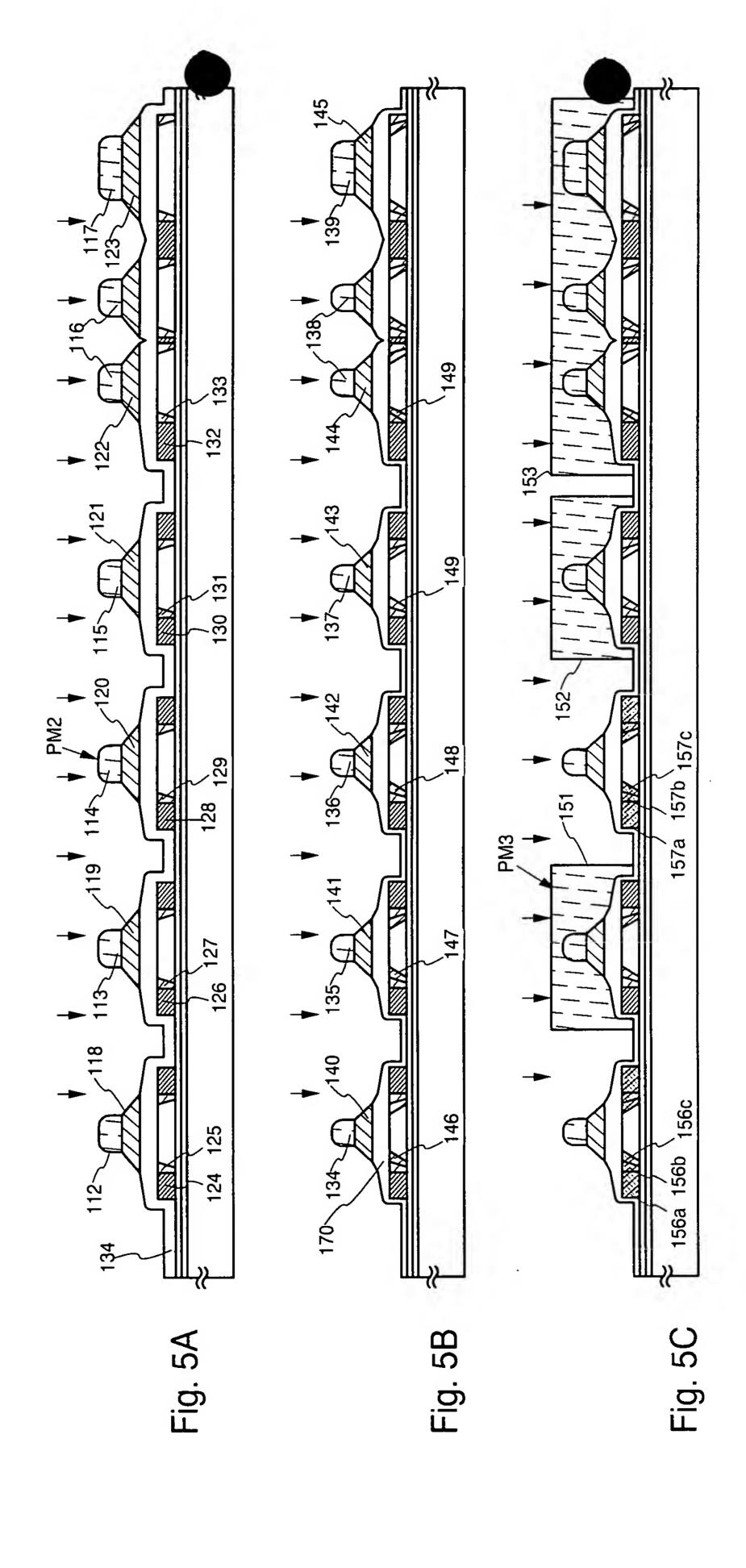
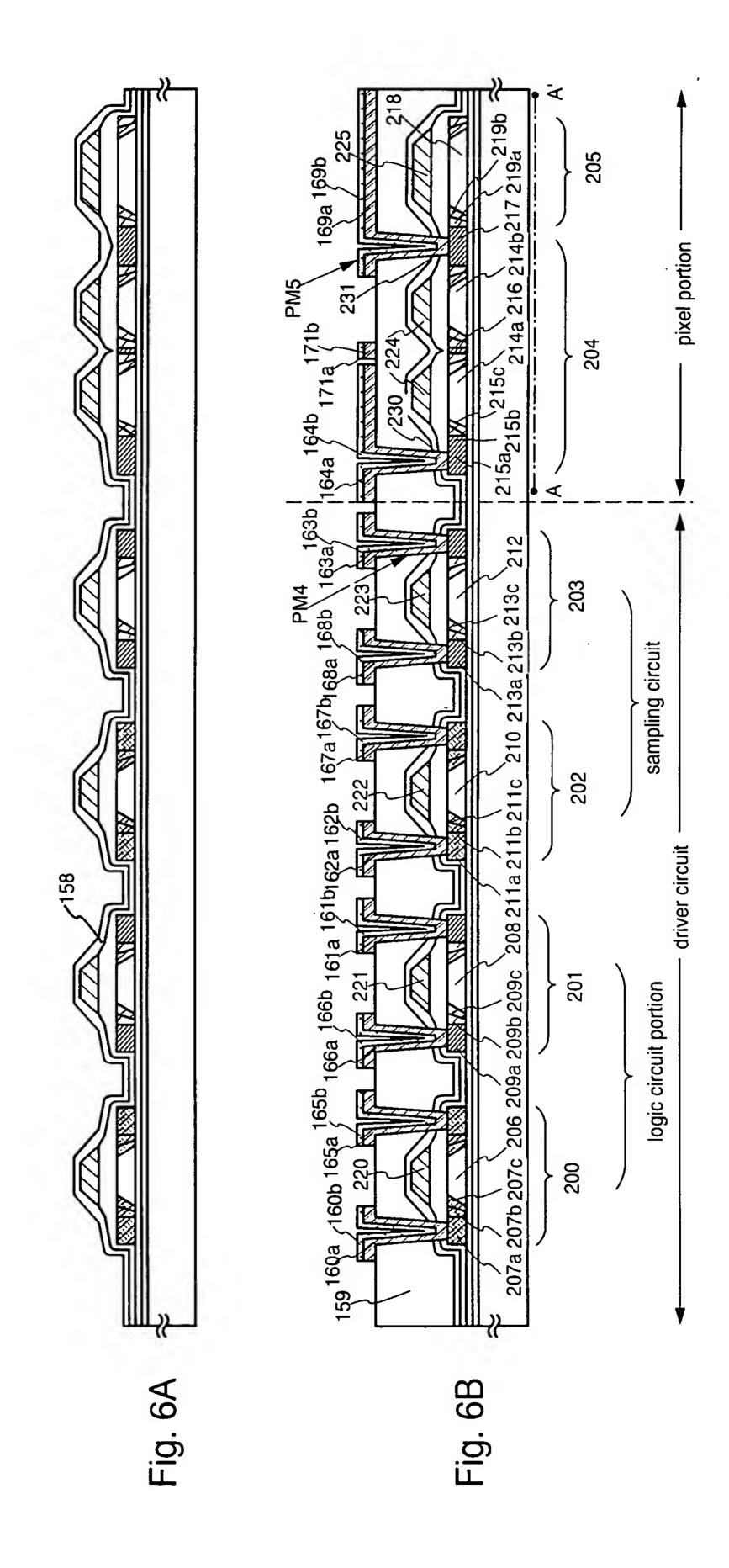
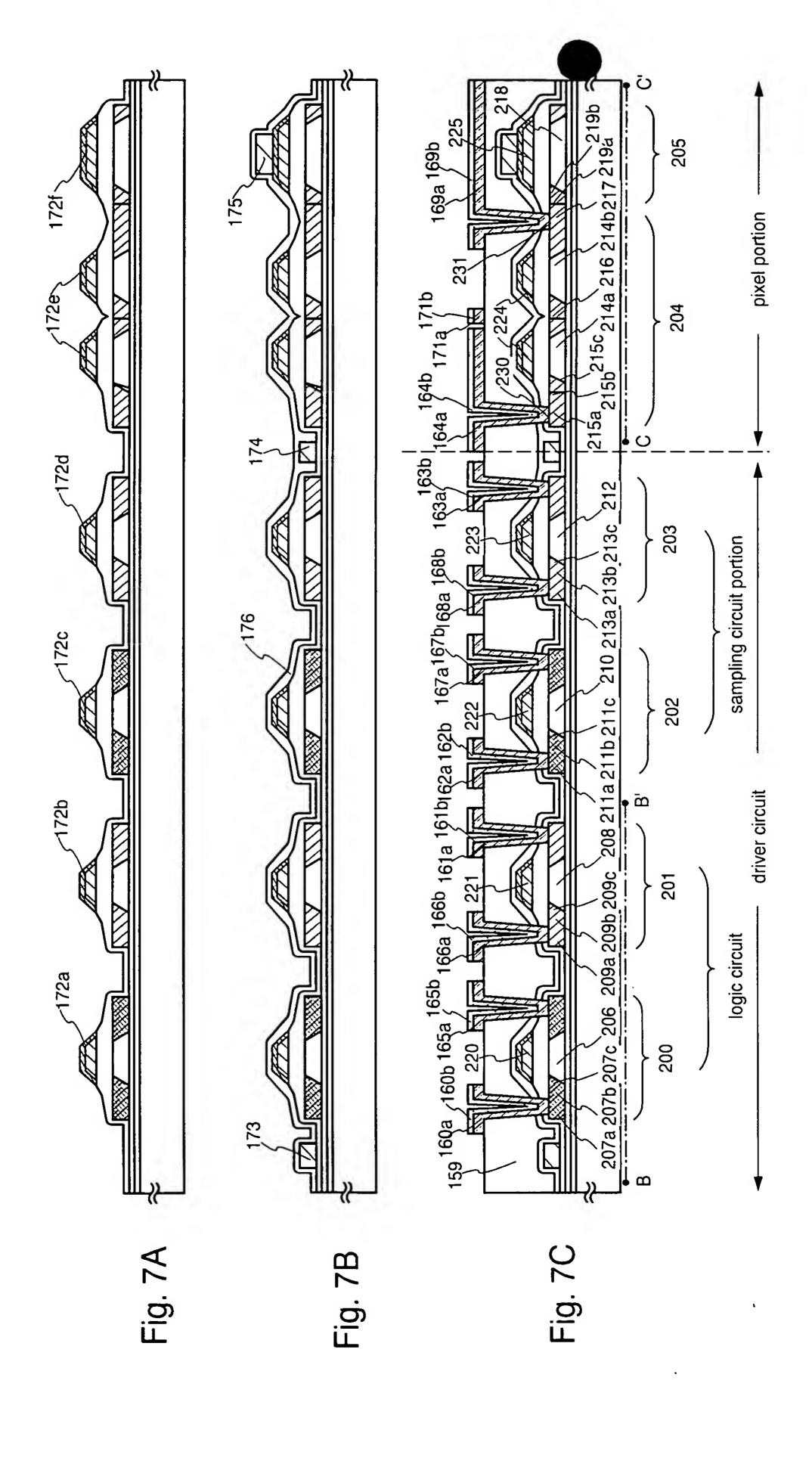


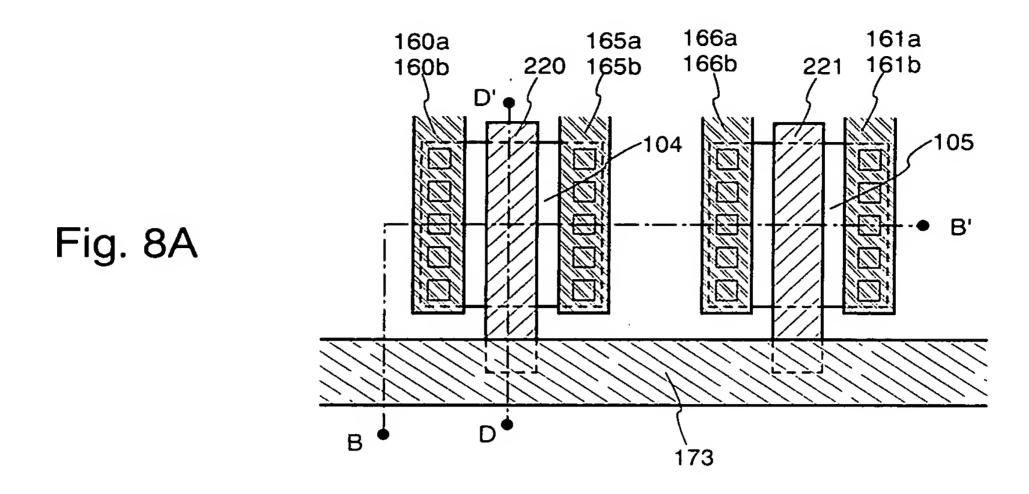
Fig. 3

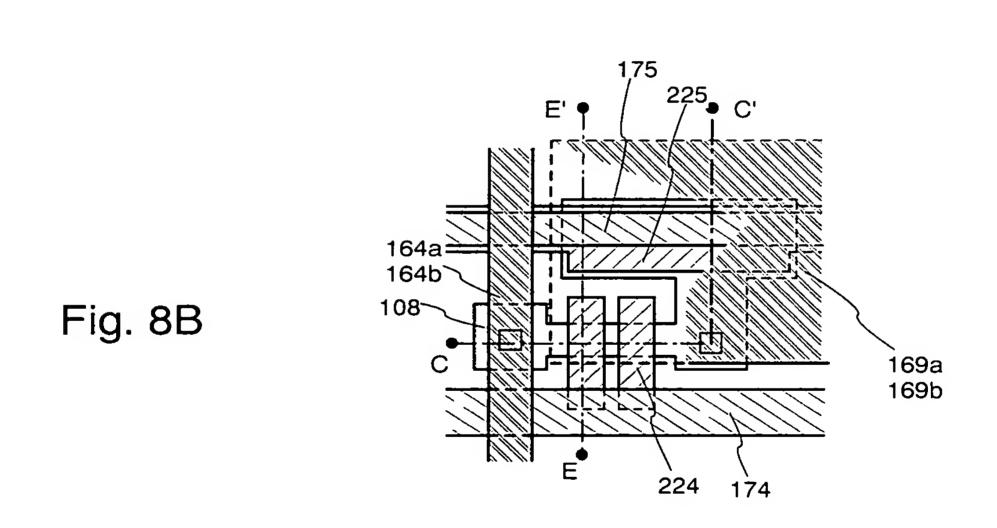


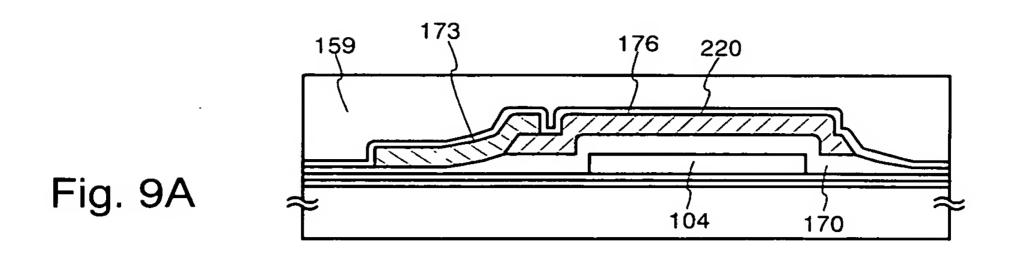


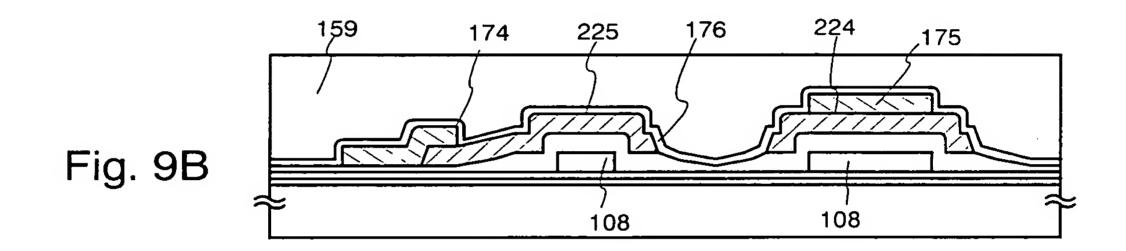


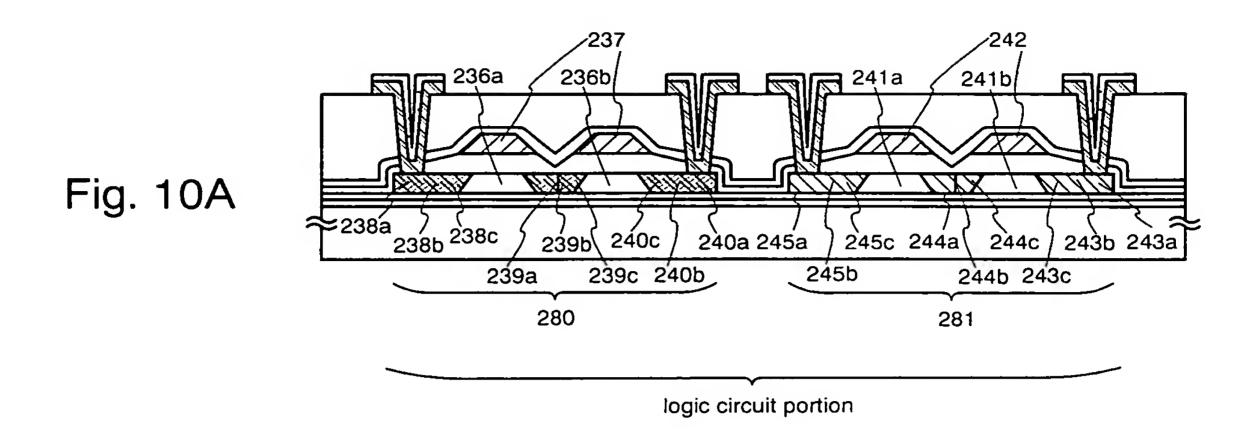


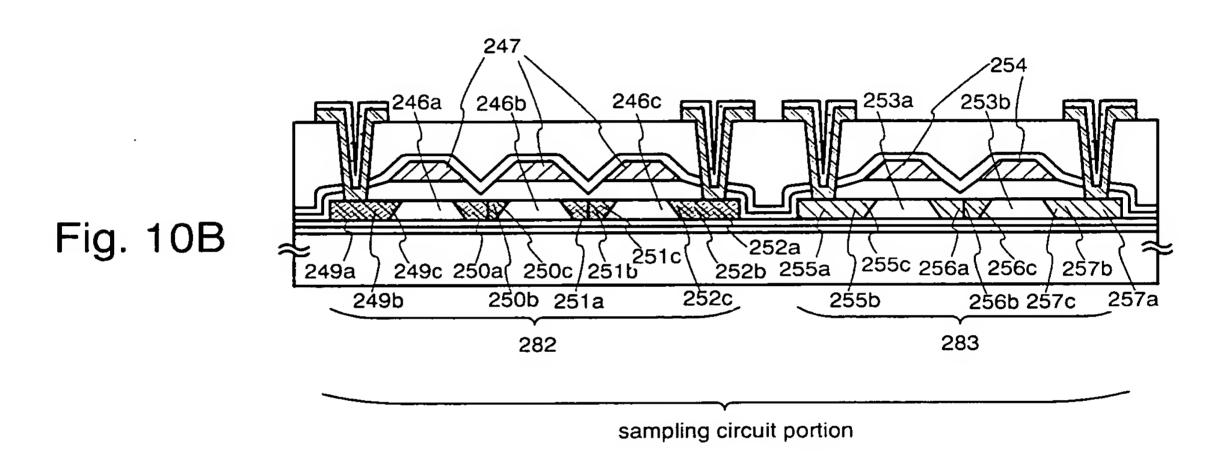


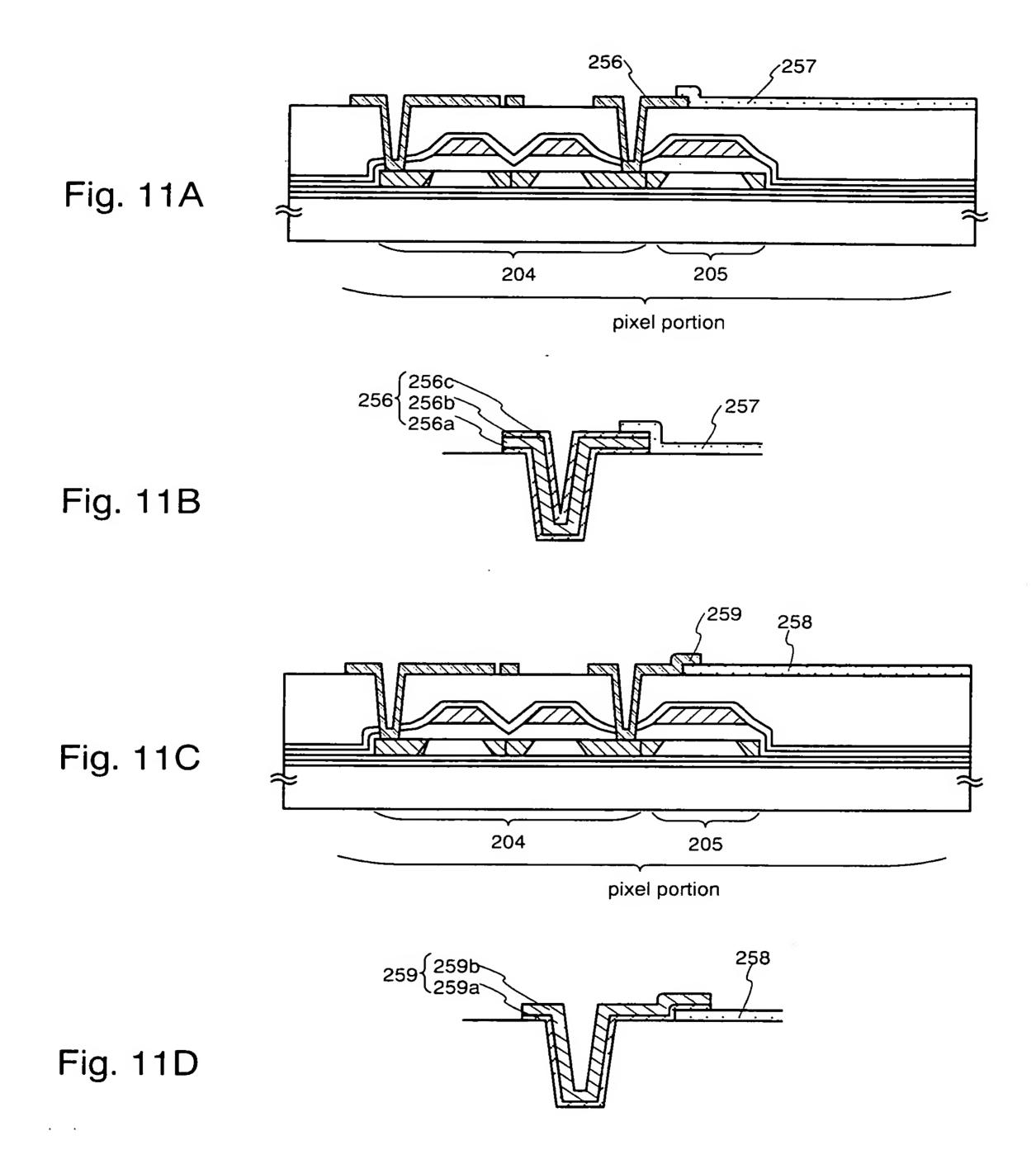












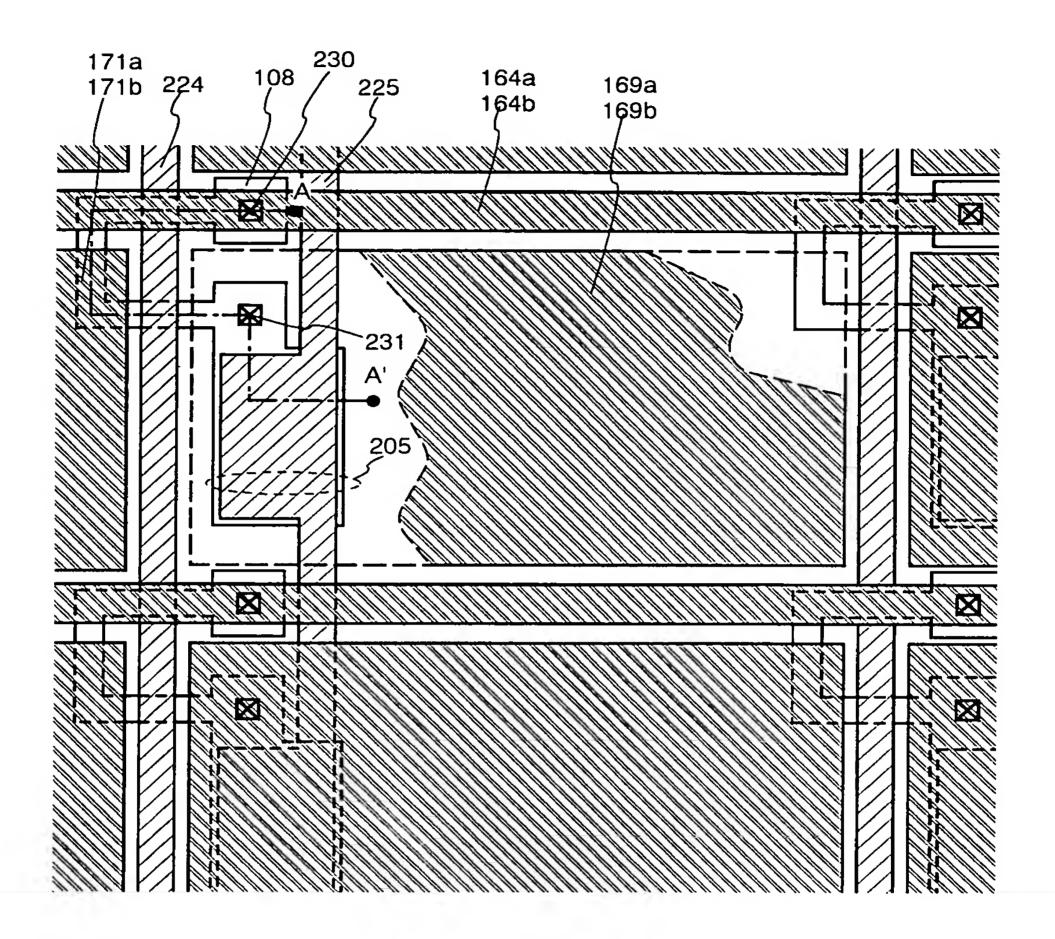
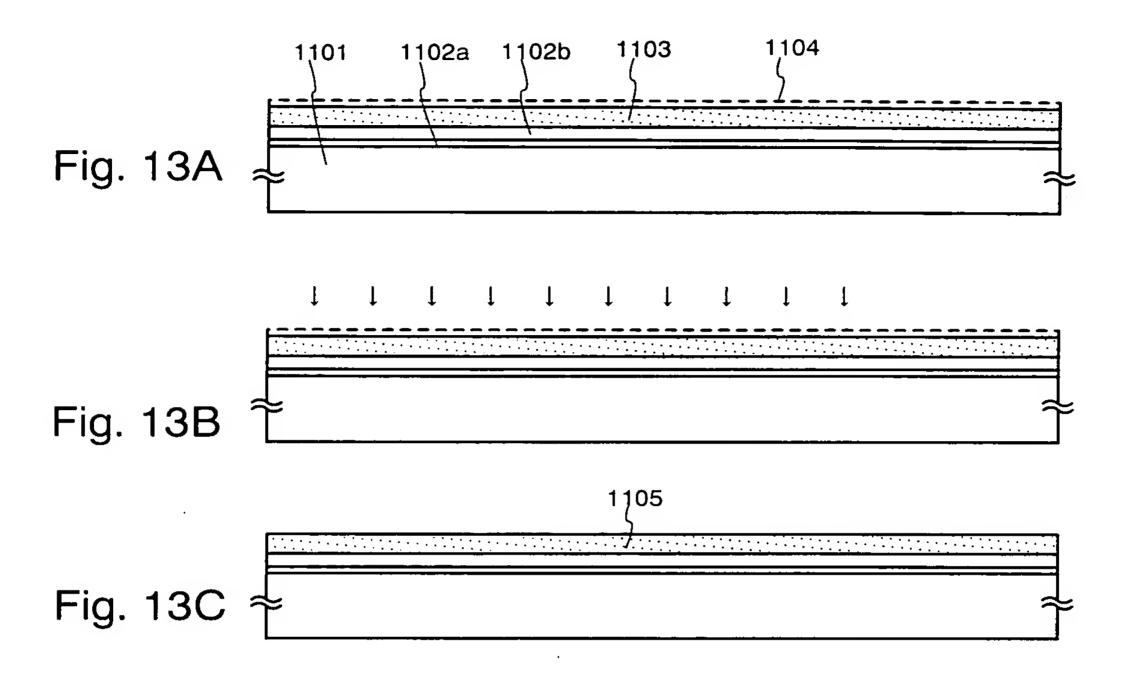


Fig. 12



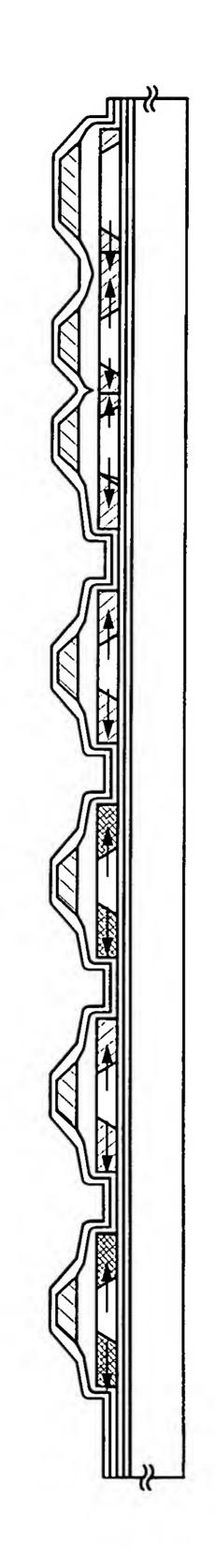


Fig. 14

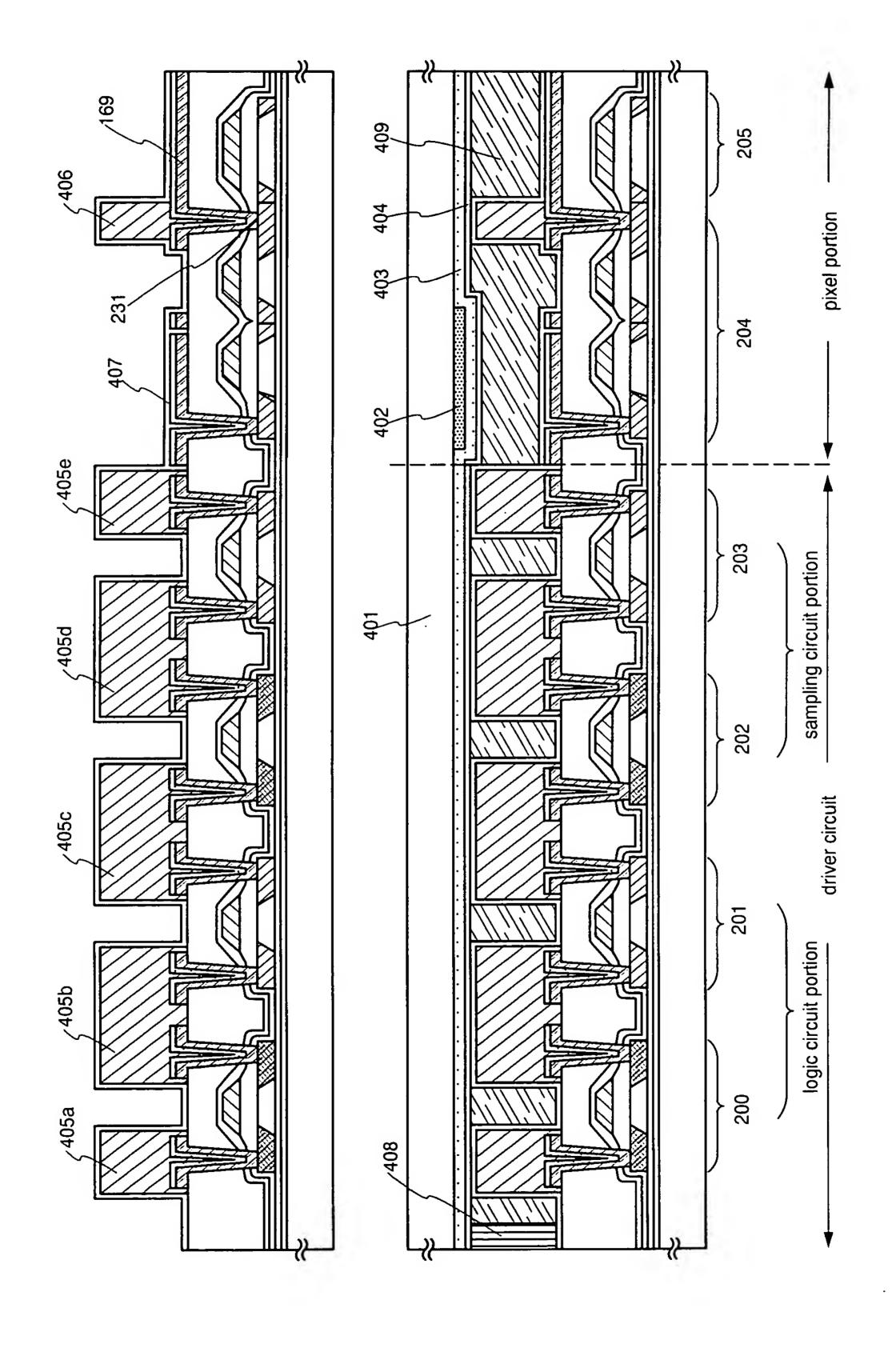


Fig. 15

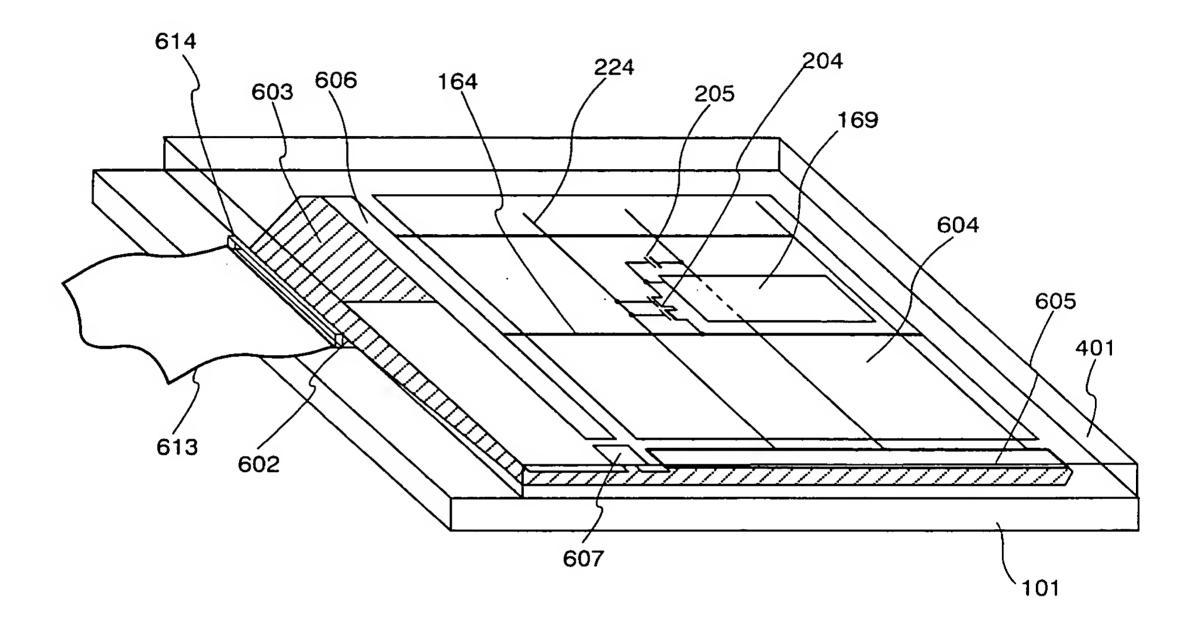
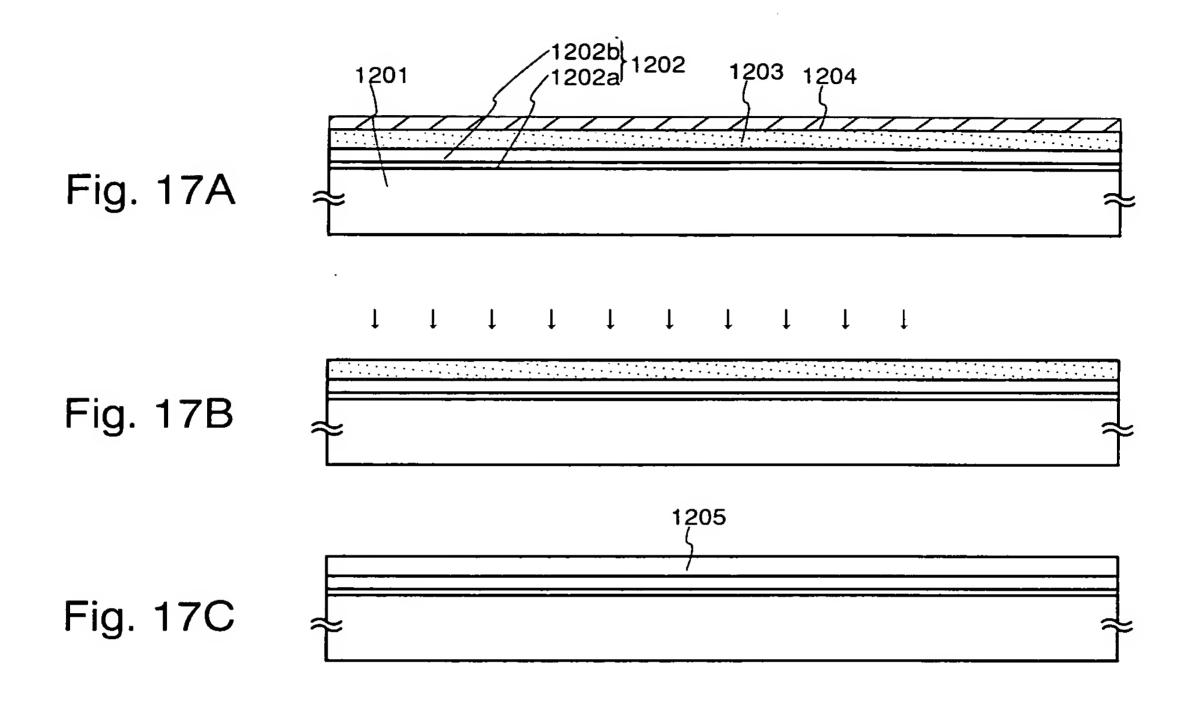


Fig. 16



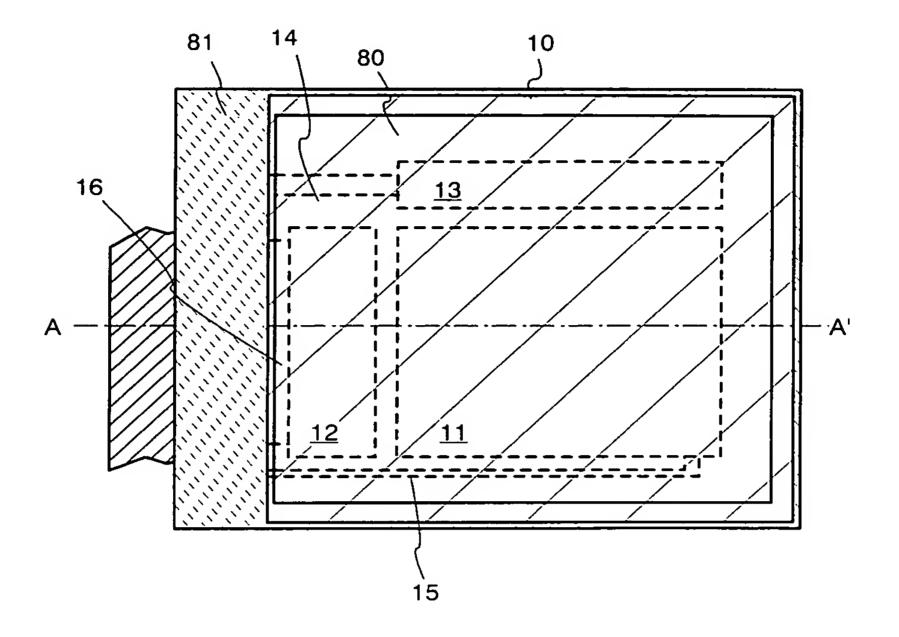


Fig. 18A

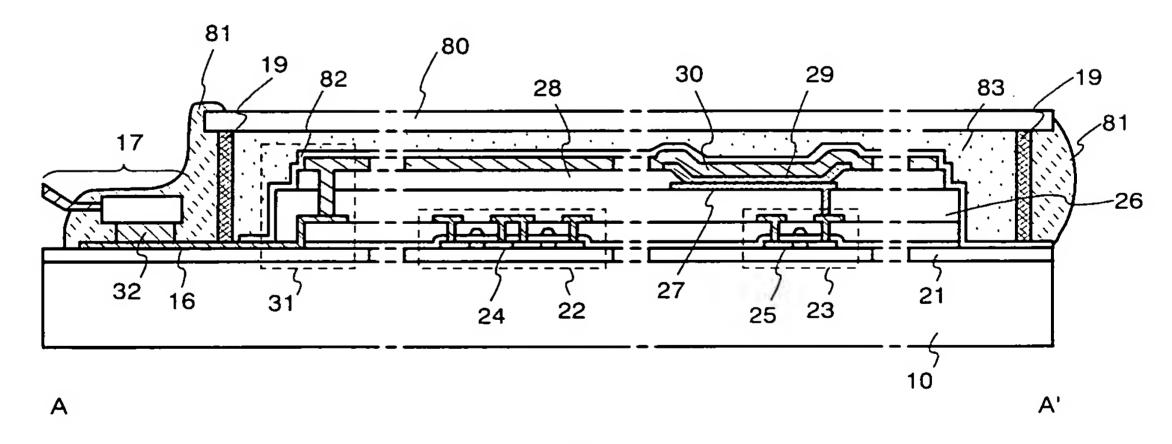
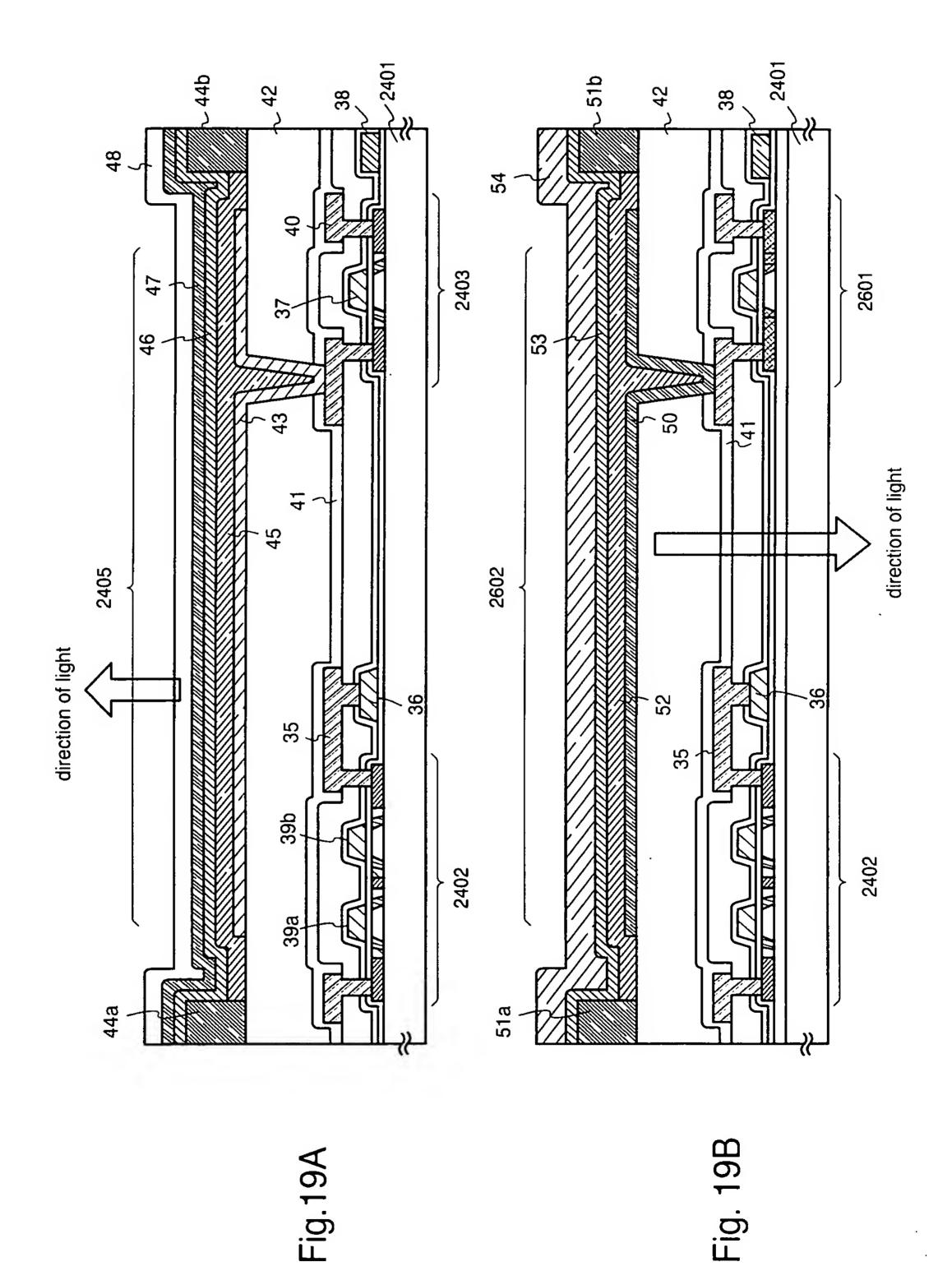
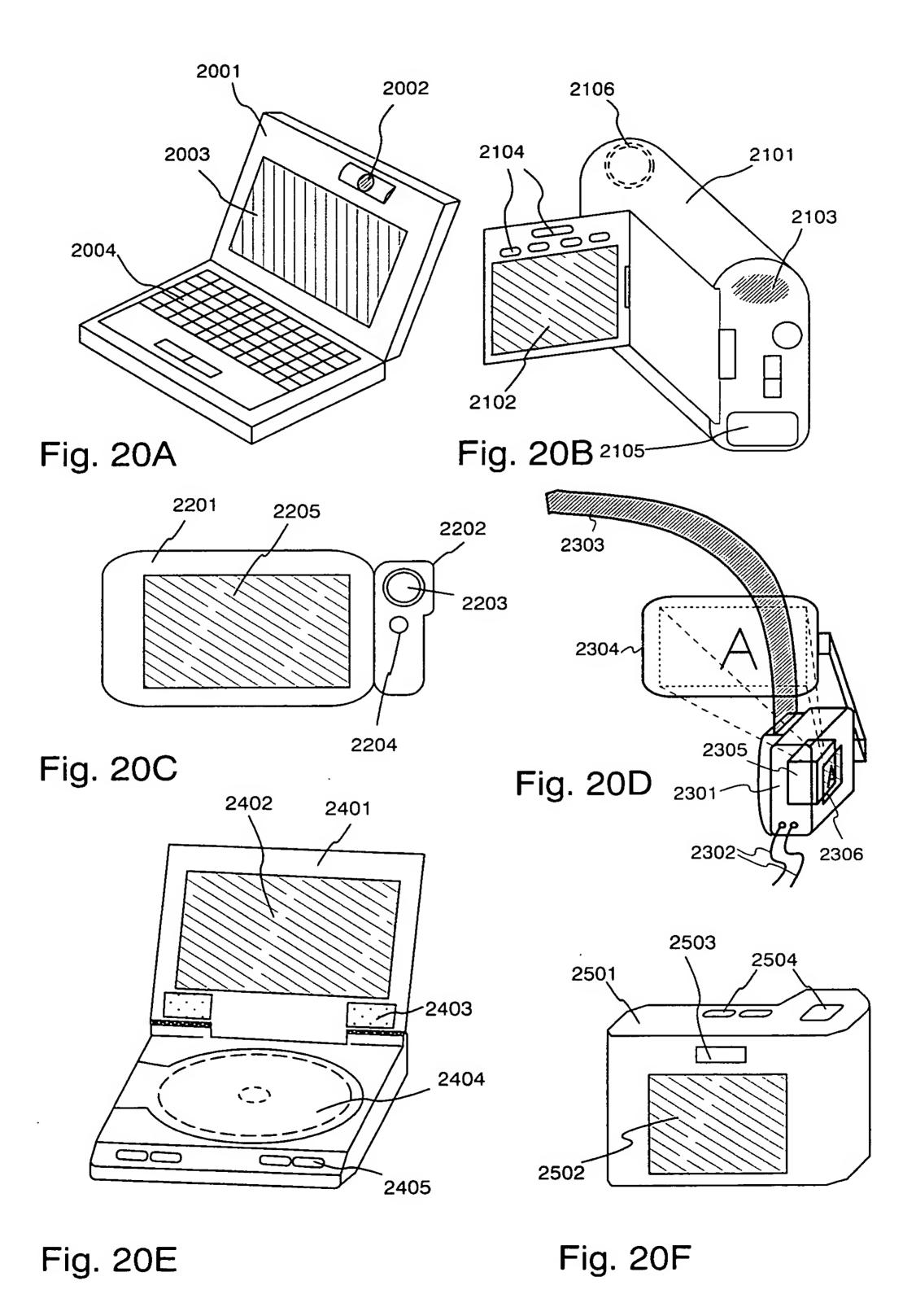


Fig. 18B





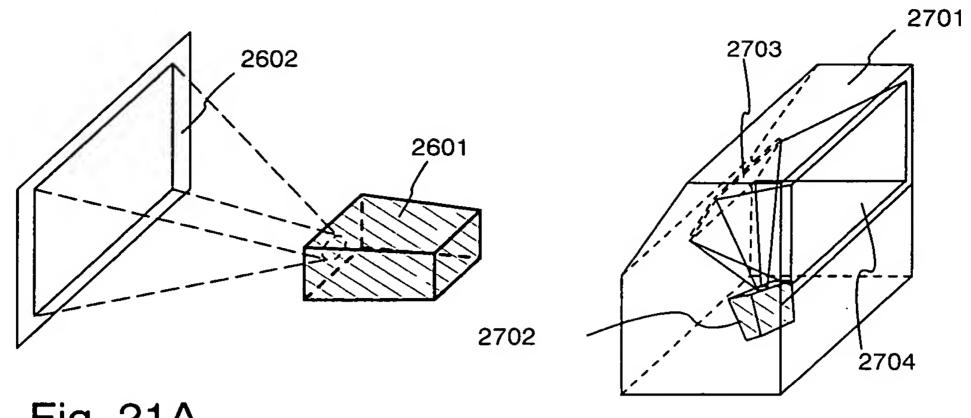


Fig. 21A

Fig. 21B

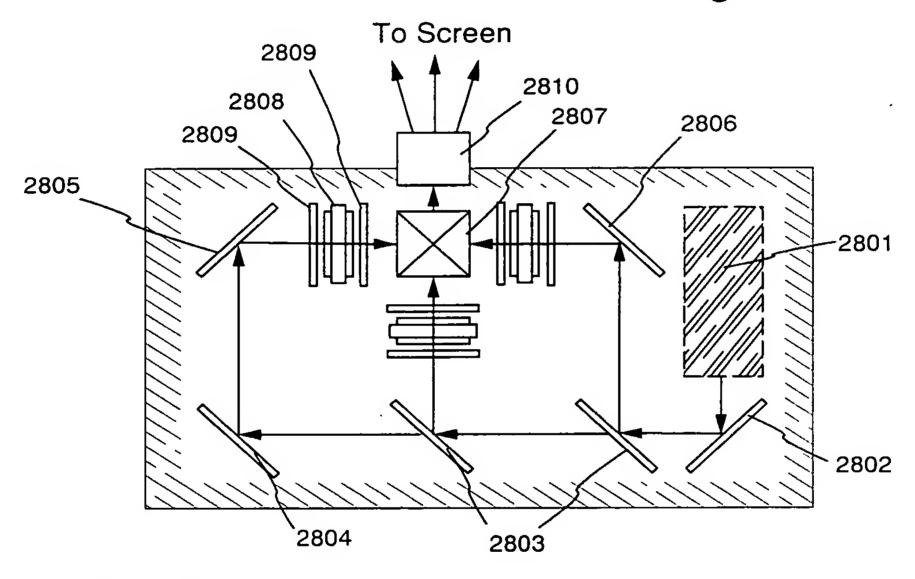


Fig. 21C

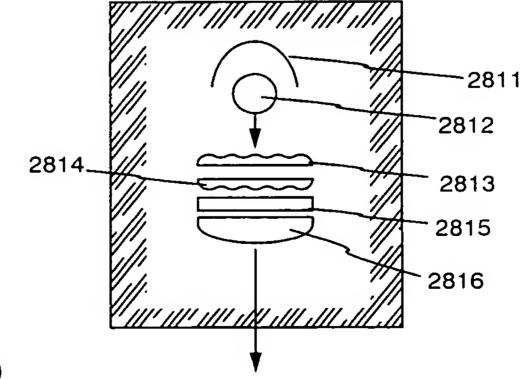
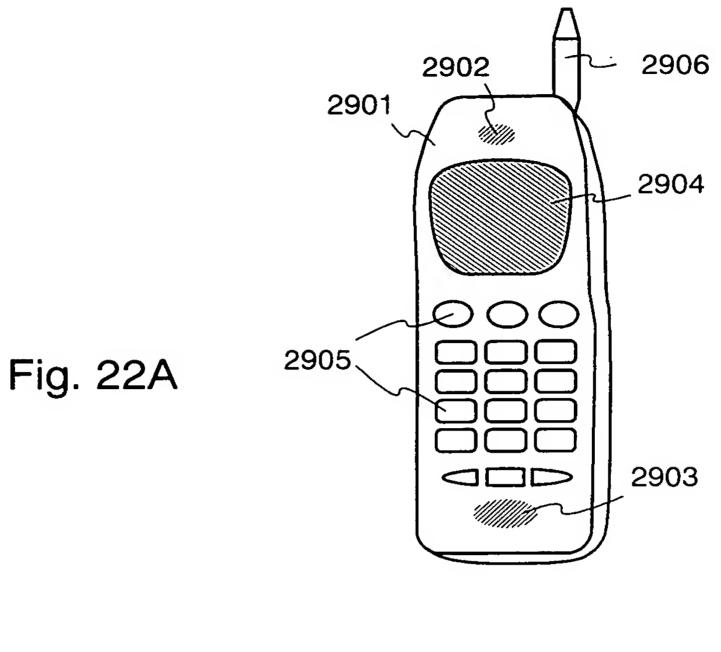
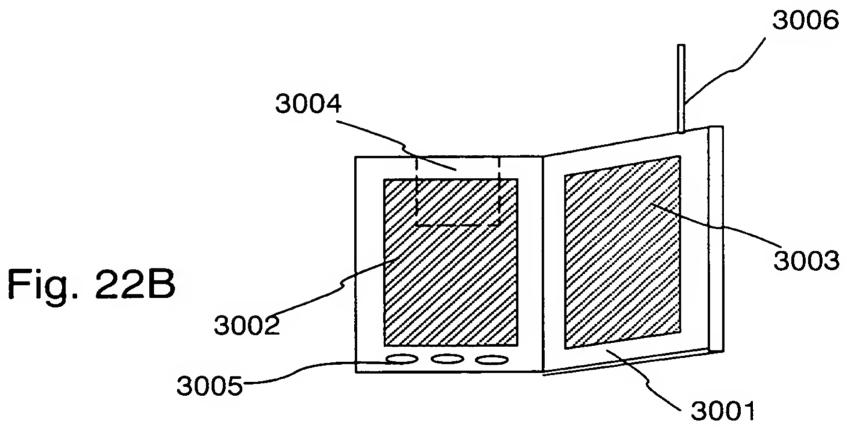
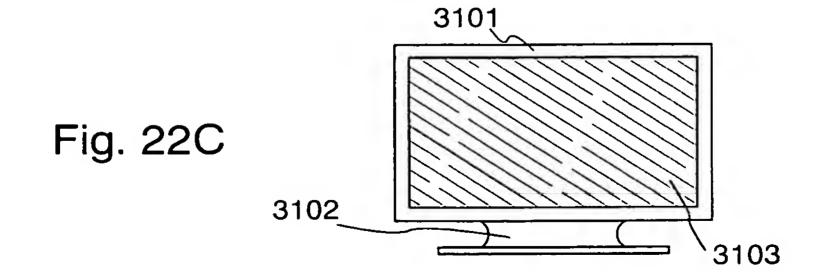


Fig. 21D







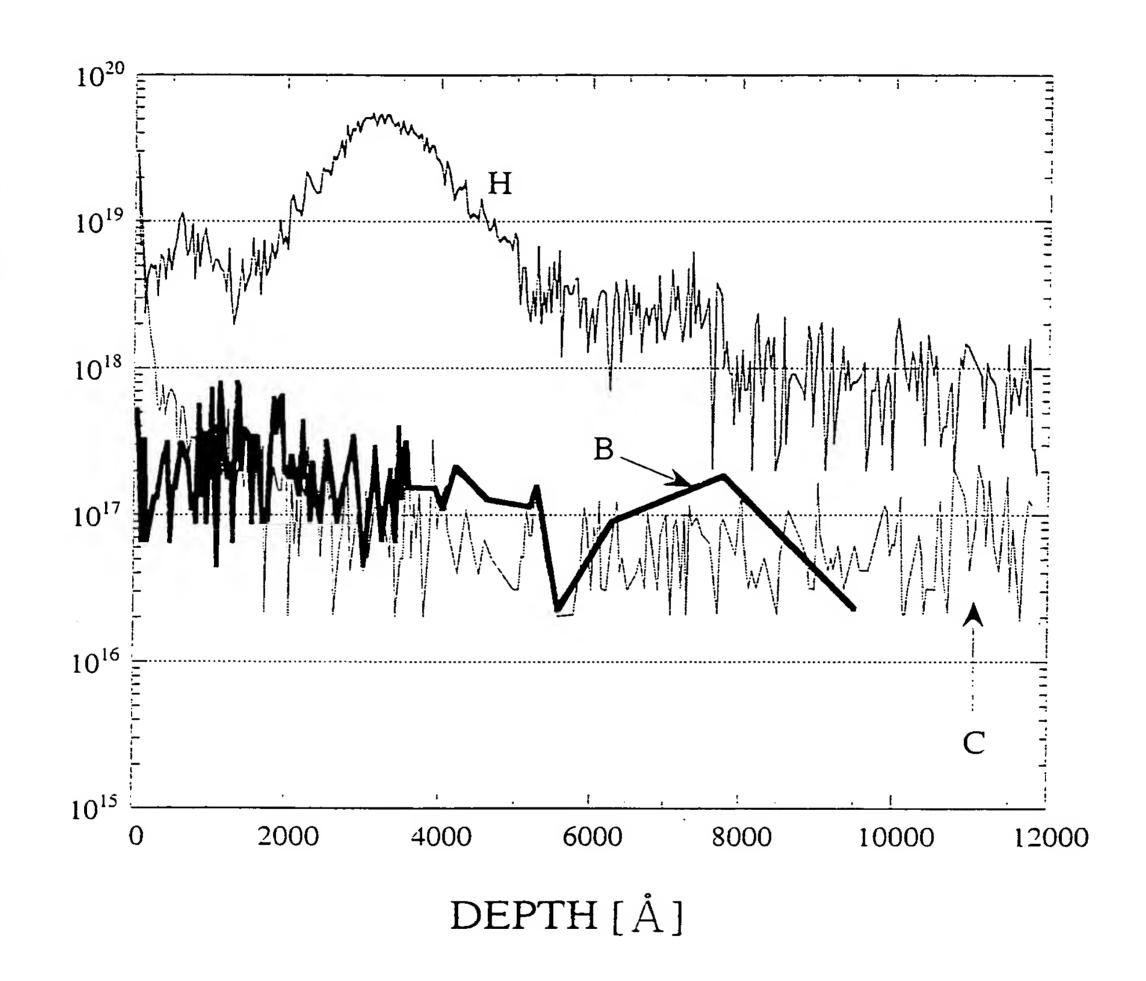


Fig. 23

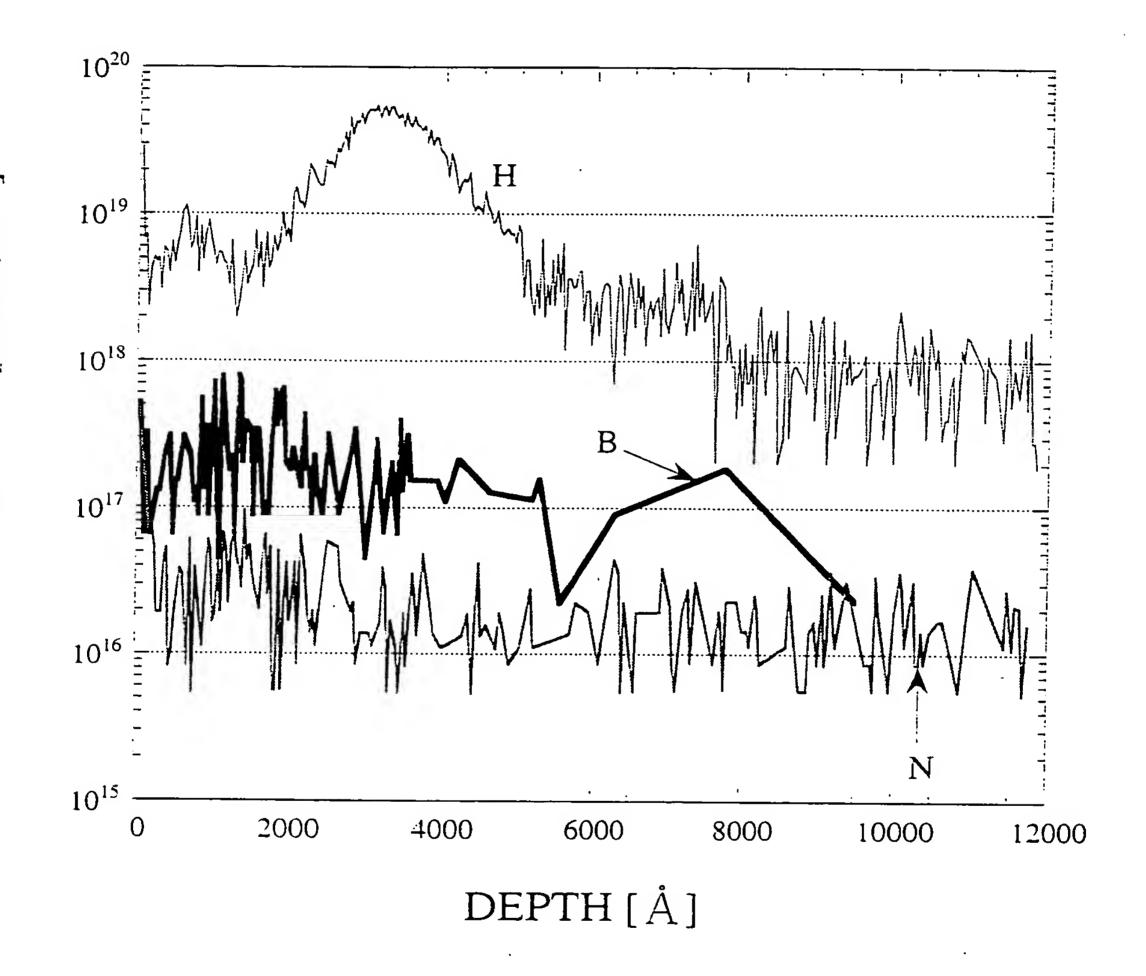


Fig. 24

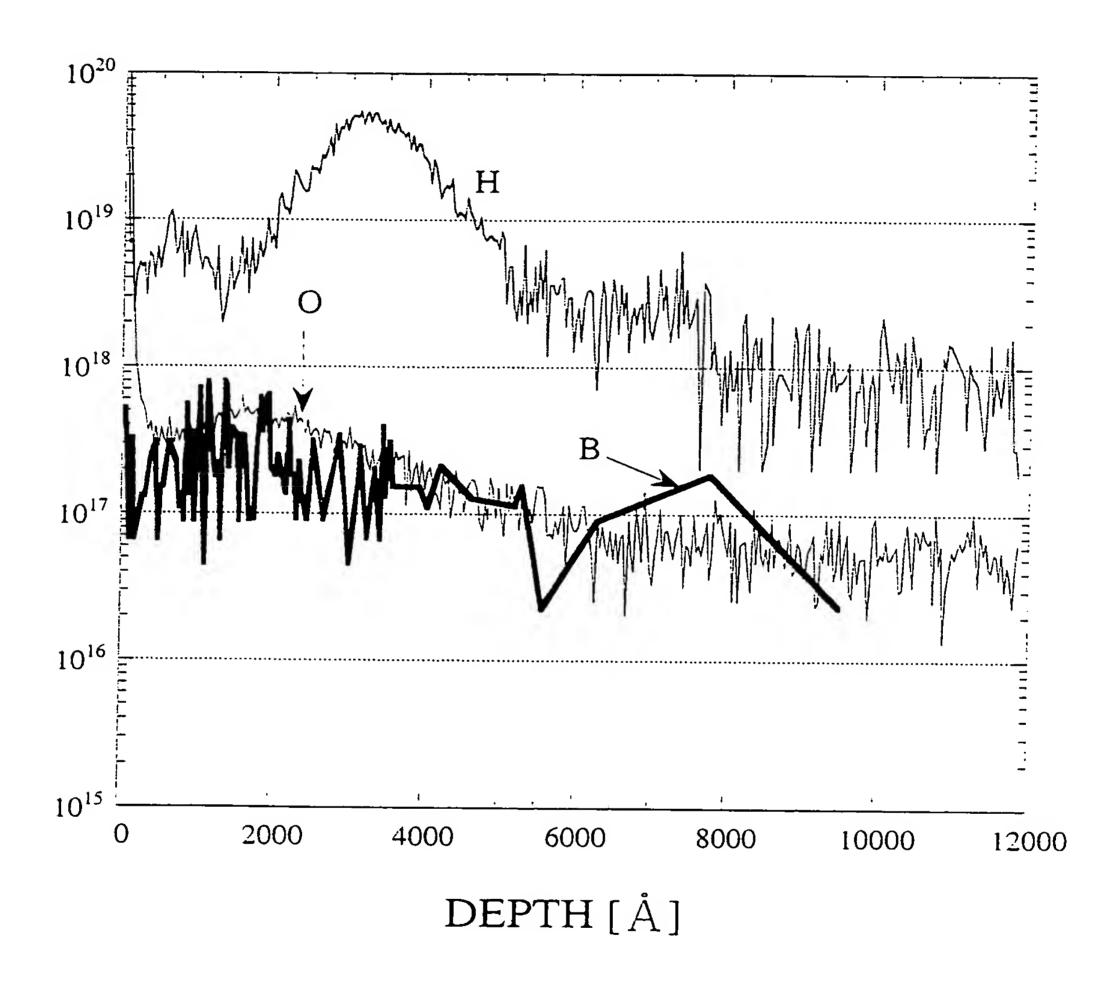


Fig. 25

CONCENTRATION[atoms/cm³]

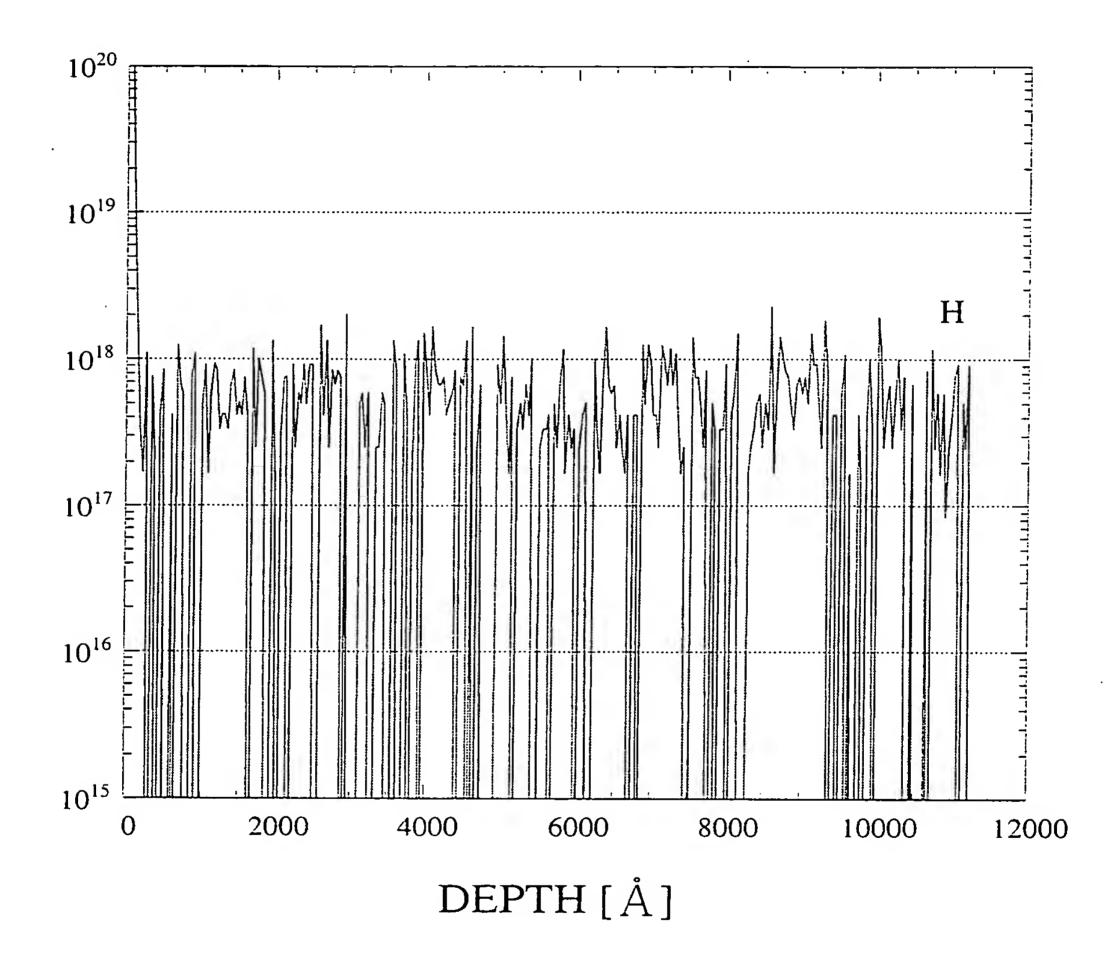


Fig. 26

CONCENTRATION[atoms/cm³]

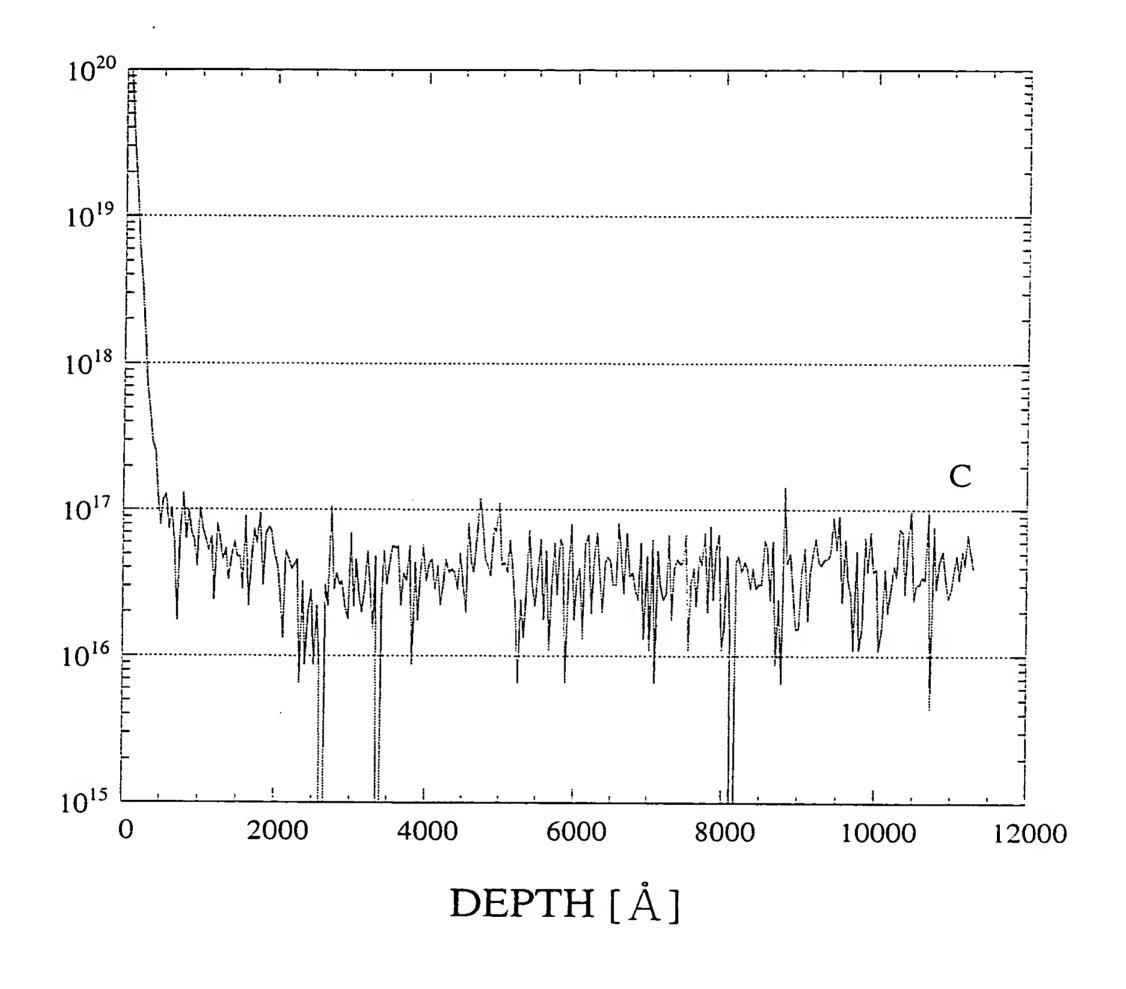


Fig. 27

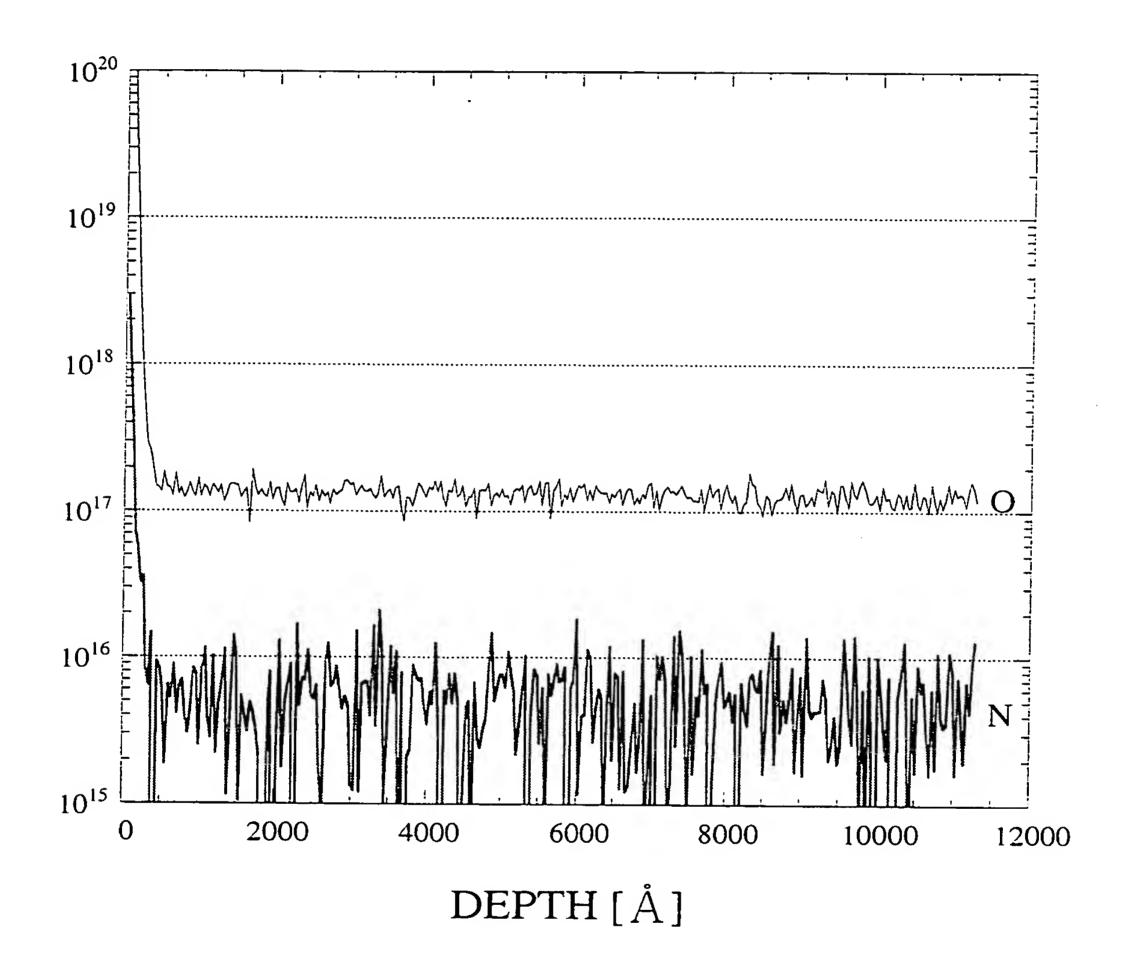
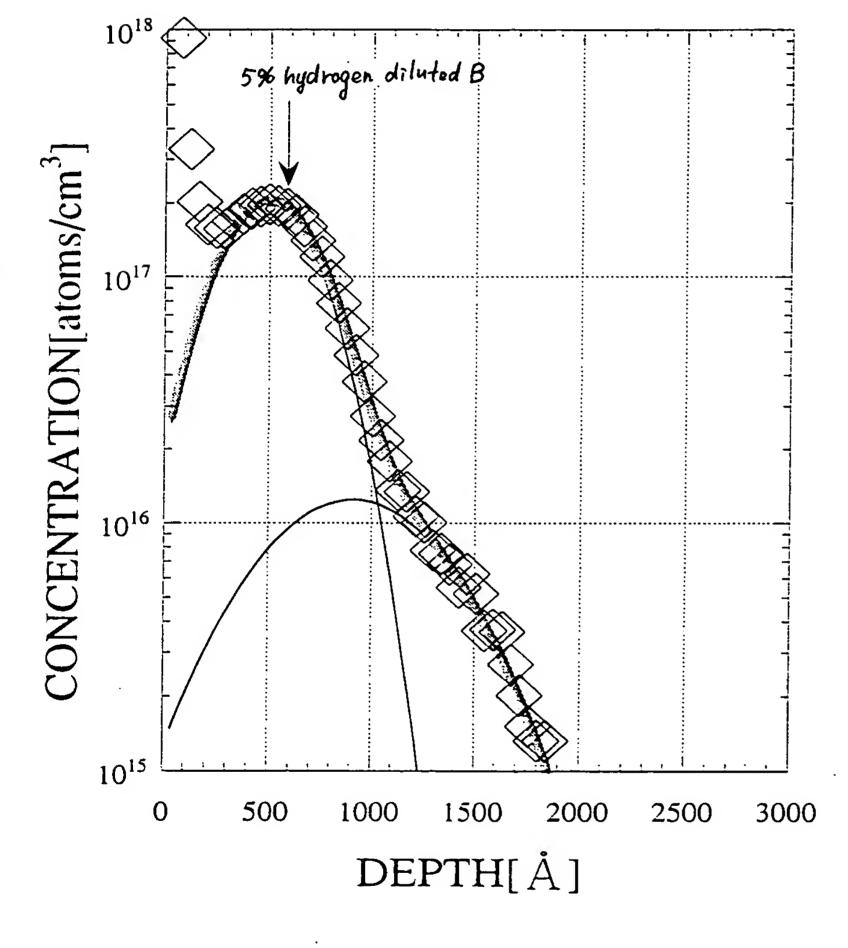


Fig. 28



	5% B fitting
	value
dosage 1	1.1224e+12
dosage 2	1.3183e+11
Standard deviation 1	227.08
standard deviation 2	422.75
projected ranges	494.37
projected range 2	908.19
X2	0.52998
R	1

Gaussian function fitting projected range of B at 30KV (Å) LSS calculation (into Si or SiO2)

 $B^+: \sim 1000 \text{ Å}$ $B_2^+: \sim 500 \text{ Å}$

Fig. 29

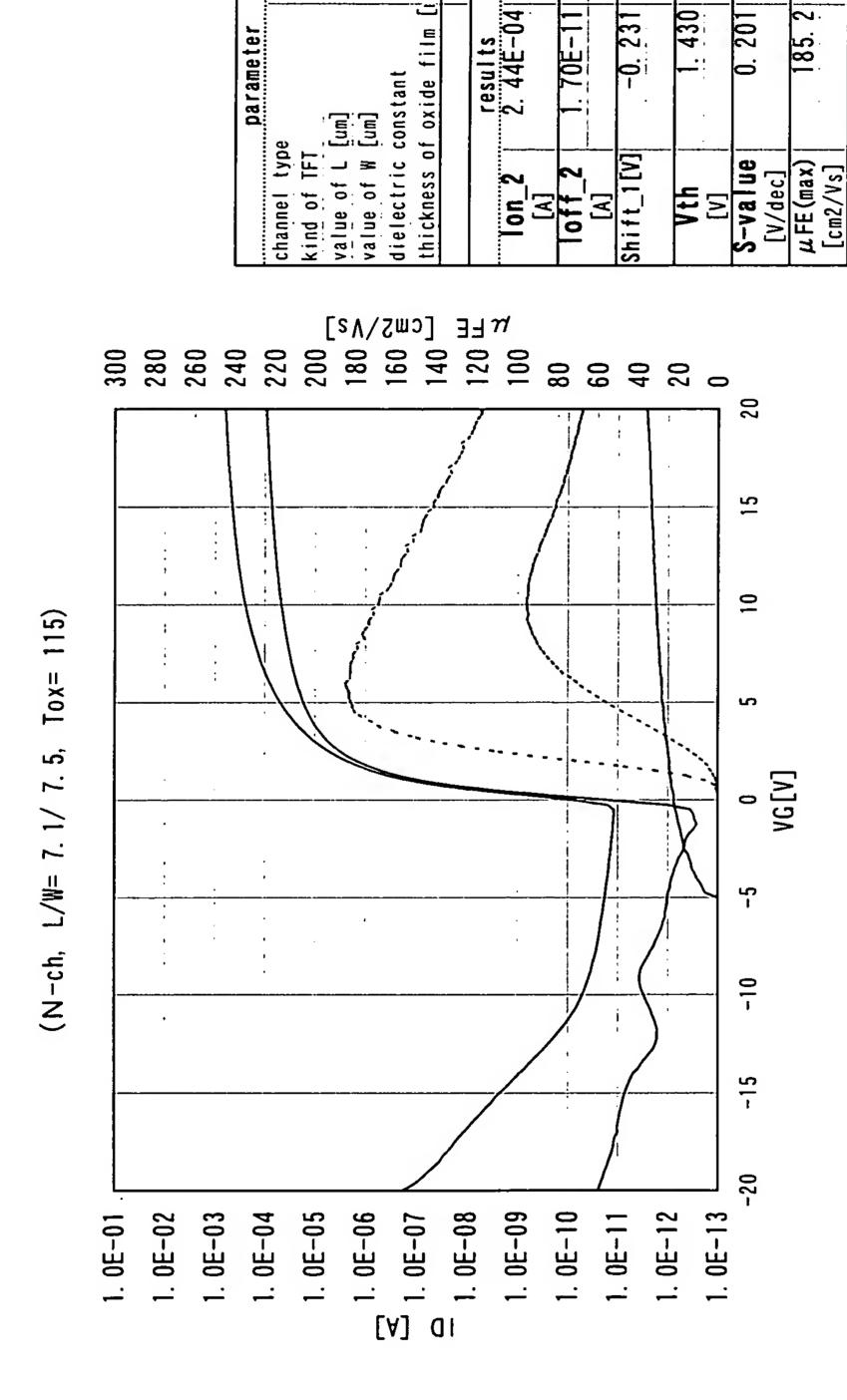


Fig. 30

of oxide film [nm dielectric constant channel type S-value μFE(max) [cm2/Vs] Shift_1[V] kind of TF value of W value of L thickness [V/dec] 10n_2 Vth Ξ 80 60 40 20 0 20 15 9 Tox = 1152 1/7.5, VG[V] (N-ch, L/W= 7.-10 -15 -20 1. 0E-02 1. 0E-10 1. 0E-05 1. 0E-06 1. 0E-12 1. 0E-03 1. 0E-04 1. 0E-08 1. 0E-09 1. 0E-07 1. 0E-01 1. 0E-11 1. 0E-13 [A] 01

results 2. 65E-04

parameters

-1.086

1. 43E-11

178.5

0.308

1.361